DUDKEVICH, B.N.

Balanced double T-type networks for measuring complex impedance components. Trudy Inst. avtom. i elektrometr. SO AN SSSR no.10:20-23 165.

Use of a phase mode for measurements in T-type bridge circuits. Ibid.:24-28 (MIRA 18:8)

DUDKEVICH, B.N. (Novosibirsk); ZHURAVLEVA, T.A. (Novosibirsk)

Conditions for the individual measurement of the components of a complex impedance. Avtometria no.3:88-96

(MIRA 19:1)

1. Submitted Feb. 23, 1965.

DUDENTICH, G.A., dote.; POSADSKAYA, G.A., assistent

Cholecystenteric fistules. Thirurgiia 34 no.9:100-101 S '58.

(MIRA 12:4)

1. Is kafedry obshchey khirurgii (sav. - dots. C.A. Dudkevich)

Yaroslavskogo meditsinskogo insitututa (dir. - prof. N.Ye. Yarygin).

(FISTULE)

DUIMEVICH, G.A., dotsent; NEDVEDKOVA, N.N., assistent

Primary and secondary localisation of echinococcosis in the female genitalia. Akush.i gin. 35 no.5:104 S-0 159. (MIRA 13:2)

1. Is kafedry akusherstva i ginekologii (saveduyushchiy - prof. Ye. K. Aleksandrov) i kafedry obshchey khirurgii (saveduyushchiy - dotsent G.A. Dudkevich) Yaroslavskogo meditsinskogo instituta.

(GENITALIA, FENALE, diseases)

(ECHIMOCOCCOSIS)

DUDKEVICH, G. A.

"Hydatid Disease According to Material from the Central Republic Hospital in the City of Ulan Bator, Mongolian People's Republic, Over a Period of 16.5 Years."

Tenth Conference on Parasitological Problems and Diseases with Natural Reservoirs, 22-29 October 1959, Vol. II, Publishing House of Academy of Sciences, USSR, Moscow-Leningrad, 1959.

Yaroslavl' Medical Institute

DUDKEVICE, G.A., dotsent

Data from a study of the possibility of an invasion of embryonic elements of Echinococcus through uninjured chitin membranes and fibrous capsule. Ehirurgiia 37 no.3:93-96 Kr 161. (MIRA 14:3)

l. Is kafedry obshchey khirurgii (sav. - dotsent G.A. Dudkevich) Yaroslavskogo meditsinskogo instituta. (TAPENOMES)

DUDKEVICH, G.A.

Brephoplastic transplantation of the skin on granulating wounds and trophic ulcers in old age. Trudy MOIP.Otd.biol.6:210-214'62.

(MIRA 16:7)

1. The Jaroslavl State Medical Institute, Chair of General Surgery.

(SKIN CRAFTING) (ACED-DISEASES)

YMTS, A.G., dotsent; DUDKEVICH, G.A., dotsent; ANDREYEV, B.I.

Surgical treatment of acute cholecystitis. Sov. med. 27 no.11: 74-78 N '63 (MIRA 18:1)

l. Iz kliniki obohchey khirurgii Yaroslavskogo meditsinskogo instituta.

YETS, A.G.; DUDKEVICH, G.A.; ZIL'BERBORD, B.Sh.; BORSHCHEVSKAYA, V.A

Potential local anesthesia in thyrotoxic goiter surgery. Sov. med. 28 no.4:45-48 Ap 164. (MIRA 17:12)

1. Klinika obshchey khirurgii (zav. - dotsent G.A. Dudkevich) Yaroslavskogo meditsinskogo instituta.

GLOWDISKI, Mieczyslaw; DUDKIEWICZ, Jan; KUDLA, Teodor

Determination of the time of labor with the aid of cytological smears. Pol. tyg. lek. 19 no.30:1148-1150 27 J1:64

1. Z I Kliniki Polomictwa i Chorob Kobiecych Sl. Akademii Medycznej w Zabrzu; kierownik : prof. dr. M. Glowinski.

OLOWINSKI, Mieczyslaw; LIPSKI, Jozef; CHRUSCIEL, Andrzej; DUDKIEWICZ, Jan

Clinical value of Smyth's test and vaginal smears in the determination of the time of labor. Pol. tyg. lek. 20 no.25:921-923 21 Je 165.

1. Z I Kliniki Polosnictwa i Chorob Kobiecych Slaskiej AM w Zabrzu (Kierownik: prof. dr. med. Miecsyslaw Glowinski).

GLOWINSKI, Mieczyslaw; DUDKIEWICZ, Jan; LIPSKI, Jozef; CHRUSCIEL, Andrzej

Relation of cytological changes of the vaginal epithelium to exogenous oxytocin. Ginek. Pol. 36 no.6:663-665 Je 165.

1. Z I Kliniki Poloznictwa i Chorob Kobiecych Slaskiej Akademii Medycznej w Zabrzu (Kierownik: prof. dr. med. M. Glowinski).

GIAWINSKI, Mieczyslaw; DUDKIEWICZ, Jan

False protracted pregnancy in the light of cytologic examinations. Ginek. Pol. 36 no.4:405-411 Ap 165.

1. Z I Kliniki Polosnictwa i Chrorb Kobiecych Slaskiej AM w Zabrzu (Kierowniki prof. dr. med. M. Glowinski).

DUDKIEWICZ, Jersy

Skin diseases, an important problem. Wiadom gorn 11 no. 1/2:39-41 Ja-F '60.

<i>DUD KIN</i> DZIUFÁI	N, N.; D	UDKIN.	غلا					 			, ,
Fish C	ulture										
Reprod	uction o	f the	Rutilus	frisii.	Ryb. k	hoz. 28 n	0. 1, 1952.	 			
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9. Monthly List of Russian Accessions, Library of Congress, April

APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7"

1952

DUDKIN, A. (Kiyev)

We have mastered the preduction of seving disks. From.keep.ne.8:21
Ag 156. (MIRA 9:10)

1.Zamestitel' predsedatelya pravleniya arteli "Metalletrud". (Kiev--Agricultural machinery)

PA 20/49138

DUDKIN, A. A.

USER/Electricity
Telegraph Equipment
Statio

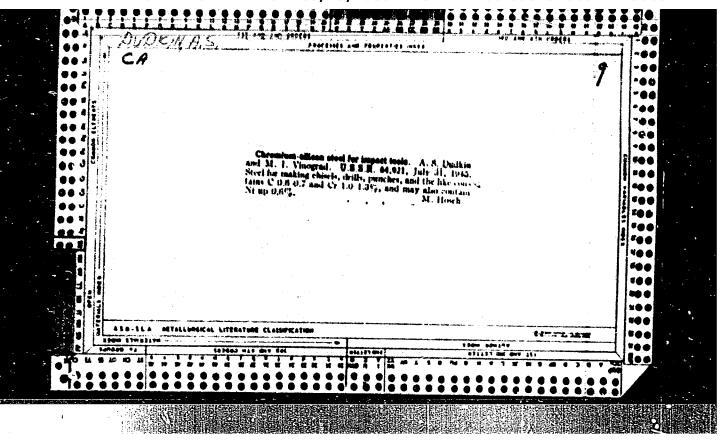
"Devices for Controlling Static in Telegraph Apparatus," A. A. Dudkin, Laureate of Stalin Prize, 2 pp

"Vest Svyazi - Elektrosvyaz'" Ho 10

Analyzes interference in the three basic systems of letter-printing apparatus: (1) synchronous apparatus with cyclic cipher (Yuz), (2) synchronous apparatus with five-place cipher (Bodo and others), and (3) start-stop apparatus (ST-35 and others). Includes four diagrams.

20/49738

"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7



"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7

- 1. DUDKIN, A. S.
- 2. USSR (600)
- 4. Spillways
- 7. Sludge ice funnel. Gidr. stroi. 22, No. 3, 1953.

9. Monthly List of Russian Accessions, Library of Congress, April 1953, Unclassified

DUDKIE, A.S., kandidat tekhnicheskikh nank.

Examining the separation of bottom alluvium by two water outlet dividers. Gidr.i mel. 5 no.5:61-70 My '53. (MLRA 6:6)

(Sedimentation and deposition)

DUDEIS, A.S., kandidat tekhnicheskikh nauk.

Operation of a sedimentation basin on a main canal. Gidr.i mel. 5 no.9:57-61 S *53. (MARA 6:9)

(Sedimentation and deposition) (Canala)

DUDKIE, A.S., kandidat tekhnicheskikh nauk; ORLOV, I.Ya., kandidat tekhnicheskikh nauk; USHAKOV, A.P., kandidat tekhnicheskikh nauk.

Some results of investigations of channel processes in sections of rivers flowing through a plain. Vop.gidr.no.l:113-124 '55.

(Hydraulics) (NLRA 9:12)

DUDKIN,A.S., kandidat tekhnicheskikh nauk

Observations on the design of the DDP-30s model of sprinkler. Sel'khosmashina no.10 0'55. (MLRA 8:12)

1. Sredneasiatskiy Mauchno-issledovatel'skiy Institut irrigatsii (Sprinklers)

DUDKIN, A.S., kand.tekhn.nauk

Use of mineralized (drainage and underground) waters for farm crop irrigation in the Golodnaya Steppe. Trudy SANIRI no.106:9-14 '60. (MIRA 14:5)

(Golodnaya Steppe—Irrigation)
(Water, Underground)

DODKIN, B.F.

Spun concrete. Gidr.i mel. 8 no.4:47-48 Ap 156.

(MIRA 9:8)

1. Starshiy inshener kontory podsobnych predpriyatiy. (Concrete construction)

DUDKIH, Fedor Ivanovich; FAIALBYEVA, T.P., red.; OUBIH, M.I., terhn.red.

[Ways of increasing labor productivity in the iron ore industry; example of miners in the Krivoy Rog Basin] Reservy povyshenike proisovditel nosti truda v shelesnorudnoi promyshlennosti; na primere rudnikov Krivoroshskogo basseina. Moskva, Isd-vo "Znanie," 1958. 38 p. (Vsesoiusnoe boshchestvo po rasprostraneniiu politicheskikh i nauchnyth snanii. Ser. 3, no.2) (MIRA 11:4) (Krivoy Rog Basin-Iron mines and mining)

DUDKIN 1.

BAKHVALOV, I., direktor; STEPANOV, V., saveduyushchiy partkabinetos; EYUEIN, S., freserovshchik-rastochnik; ENEMCERATOV, V., inzhener; KOZHEVNIKOVA, M., nachal'nik tokarno-otdelochnogo otdeleniya, laureat Stalinskoy premii; UL'YANOV, M., predsedatel' tsekhkoma sborochnogo tsekha; MAUHOV, A., brigadir komsomol'sko-molodeshnoy brigady; DUDKIN, I., dotsent, direktor; ZHUKOV, P., tokar'.

[In a progressive plant; accounts of workers and technical engineering workers of the Moscow Order of the Red Banner of Labor Second State Bearing Plant] Ha peredovom mayode; rasekany rabochikh i inmenerno-tekhnicheskikh rabotnikov Moskovskogo ordena Trudovogo Krasnogo Znameni 2-go Gosudarstvennogo podshipnikovogo mayoda. [Moskva] Profindat, 1952. 94 p. (MERA 615)

1. Moskovskiy ordena Trudovogo Krasnogo Knameni vtoroy Gosudarstvenny, podshipnikovyy savod. 2. Vecherniy mashinostroitel'nyy institut (for Dudkin). (Efficiency, Industrial)

Dudkin, I.A.

ATAMANCHUKOV, G.D.; GORBUNOV, I.G.; DUDKIN, I.A.

Experimental data on pressure-operated resin-extracting batteries. Giárolis. 1 lesokhim.prem. 8 me.5:18-19 '55. (1:0 AEIK)

1.TSentral'nyy nauchno-iseledovatel'skiy lesekhimicheskiy institut (for Atamanchum., Gorbunev, Dudkin). (Gume and resins) (for Atamanchukev). 2. Nevo-Belitskiy lesokhimicheskiy kombinat (for

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DEDKIN, L. D.

DUDKIN, L. D. --"Investigation of the Thermoelectric Properties of Cobalt Antimonides." Inst of Metallurgy imeni A. A. Baykov, Acad Sci USSR. Moscow, 1955. (Dissertation for the Degree of Candidate in Technical Science).

SO Knizbanay letopis' No 2, 1956

137-58-4-8073

Translation from: Referativnyy zhurnal, Metallurgiya, 1958, Nr 4, p 243 (USSR)

AUTHORS: (Dudkin, L.D., Abrikosov, N.Kh.

137-58-4-8073

An Investigation of the Thermoelectric Properties of Cobalt Antimonides

thermal conductivity of the alloys. The existence of a new compound, E-CoSb3, formed by a peritectic reaction at 859°C, was established. It has a body-centered cubic lattice of the type of skutterudite [(Co, Ni)As3](a= 9.01 angstrom, Fedorov group l_n^5). Curves for the relation to temperature of the specific conductivity and the thermoelectromotive force for alloys similar in composition to the compounds CoSb3 and CoSb2 demonstrate the latter to be semiconductors. The width of the forbidden region in CoSb2 and CoSb3 is 0.2 and 0.5 electron volt, respectively, and the thermal conductivity rate of the lattice is 11.10-3 and 12.3.10-3 cal/degree C.cm. sec. respectively. The electron mobility in the CoSb₃ lattice is 290 cm²/v sec. Investigations of the Co-Ni-Sb ternary system have revealed a continuous series of solid solutions between the phases of the binary systems and the terminations of a number of solid solutions based on the \mathcal{E} -CoSb3 compound. The ternary solid \mathcal{E} solution spreads deep into the triangle of concentration until attainment of Ni: Co= 1:9. The C of the g phase increases with increase in the Ni content, as the Ni apparently forms donor levels with low energies of activation in the forbidden region of CoSb3, and yields excess electrons to the conducting region at relatively low temperatures, in which case the thermal conductivity of the lattice diminishes considerably. The temperature dependence of the C and the thermoelectromotive force also change significantly. Card 2/2 P.S.

DUDKIN, L.D

USSR/Physical Chemistry - Thermodynamics, Thermochemistry, Equilibria,

Physical-Chemical Analysis, Phase Transitions. B-8

Abs Jour: Referat. Zhurnel Khimiya, No 2, 1958, 3799.

Author : L.D. Dudkin, N.Kh. Abrikosov.

Inst :

Title : Study of Nickel Influence on Properties of Semiconductor

Compound CoSb .

Orig Pub: Zh. neorgan. khimii, 1957, 2, No 1, 212-221.

Abstract: The influence of Ni additions on the properties of the semiconductor compound CoSb3 discovered by the authors (RZh-Khim, 1957, 71107) was studied. The measurement of thermo-electrical properties indicates a pre-eminent metallic nature of atom bonds in NiSb and NiSb4. An isotermal section of the ternary system Co-Ni-Sb in the range of less than 50% of Sb confirms the existence of a continuous solid solution between the 2'-

phases of the binary systems. The existence of a ternary solid

Card : 1/2

-37-

USSR/Physical Chemistry - Thermodynamics, Thermochemistry, Equilibria, Physical-Chemical Analysis, Phase Transitions.

B-8

Abs Jour: Referat. Zhurnal Khimiya, No 2, 1958, 3799.

E-solution on the CoSb3 base was established; the Ni saturation limit thereof corresponds to the ratio Ni : Co = 1 : 9. Ni introduced into CoSb3 produces donor admixture levels, which are completely ionized at room temperature. The electron mobility in CoSbjis considerably increased at Ni : Co < 15. The electron mobility decreases at higher Ni concentrations in consequence of a substantial diffusion of electron waves by Ni ions. The lattice heat conductivity of the & -phase drops with the Ni concentration rise.

Card : 2/2 -38-

DUDKIN, L.D.

AUTHOR:

Dudkin, L. D..

57-2-5/32

TITLE:

The Chemical Bond in Semiconducting Cobalt Triantimonide (Khimiches* kaya svyaz' v poluprovodnikovom triantimonide kobal'ta).

PERIODICAL:

Zhurnal Tekhnicheskoy Fiziki, 1958, Vol. 28, Nr 2, pp. 240-244 (USSR).

ABSTRACT:

Starting from the conceptions of a predominantly covalent nature of the bonds between the atoms in electron-semiconductors an approximate image of the chemical interaction in the compound CoSb₃ discovered by the author and his collaborators and described in reference lo is given here. CoSb₃ (C-phase) develops according to the phase-diagram (reference lo) in the reaction in a peritetic at 859°C. At the isothermal lines of thermoelectric properties of the cobalt-antimony alloys the compound composition shows highly distinct maxima of the electric resistance and the thermoelectromotive force with a negative sign. The temperature-mean surements of the electric conductivity showed that the CoSb₃-compound

is a semiconductor with an activation—energy of the current—carriers equal to 0,19 eV. The £-phase possesses a small domain of homogeneity. The deviation from the stoichiometric relation in the direction of an excess of antimony in individual samples, in the case of small (from

Card 1/4

The Chemical Bond in Semiconducting Cobalt Triantimonide.

57-2-5/32

O to +30 MV/°C) values of the coefficient of the thermoelectromotive force leads to a reversal of signs concerning the conductivity (All "ho= le "-alloys of the &-phase contain small quantities of eutectic, i. e. they are saturated with regard to antimony). The X-ray investigations of the structure (reference lo) showed that the CoSb3-compound is isomorphous with the mineral scutterudite CoAs, (reference 11). Starting from the conceptions on a covalent nature of the semiconductor-bonds and the data on the crystal-structure of GoSb, the valence-states of the electrons in the cobalt- and antimony-atoms which lead to the formation of the semiconductor-bonds in the molecular structure Co . Sb 1 3 and in the crystals of the E-phase of equal composition are schematically given here. Two schemes are suggested (figures 3 and 4). The first scheme is based on the assumption of a double-compound corresponding to the C-phase of Co2Sb6. This scheme is in agreement with the crystallochemical characteristics of the t-phase, but contradicts the occurrence of the hole-conductivity in the compound in the case of antimony-excess (a deficiency of cobalt-atom in the lattice). The second scheme of the electron-valence-states of the atoms in a molecule of ordinary CoSb, does not contain these contradictions. It also explains the occurrence of the hole-conductivity in the case of antimony-

Card 2/4

The Chemical Bond in Semiconducting Cobalt Triantimonide.

57-2-5/32

excess: the absence of the cobalt-atom in the lattice leads to the formation of three holes in the valence zone, as the antimony-electrons participating in the formation of linkages with this atom remain connected with the neighboring cobalt-atoms (the coordination of antimony with regard to cobalt equals two). The deficiency of this scheme is a certain income gruity between the nature of the antimony-bonds (Sp-bonds) and the value of the valence-radius in the lattice (tetrahedron) in antimony. On the tasis of the investigation given here the conclusion is drawn that the semiconductor-alloys of the g-phase with antimony-excess with regard to stoichiometry show a peculiar nature. It is shown that the positive cure rent-carriers of admixtures in CoSb₃ in the case of antimony-excess accor-

ding to the scheme (figure h) are not activated - but concentration-current-carriers. I. e. they develop due to the formation of a defective latatice in the case of a deviation of the concentration from the atomic relation Co: Sb = 1:3. Therefore the number of these current-carriers of admixture (in case that changes of concentration do not take place in the alloy) will not change with temperature. At a temperature close to the absolute zero the occurrence of superconductivity (like in metals) is to be expected in such materials. Inversely, at high temperatures where the activation of the own current carriers prevails the electric conductivity

Card 3/4

The Chemical Bond in Semiconducting Cobalt Triantimonide.

57-2-5/32

increases according to the usual behavior of the semiconductor. - The results of the alloying of the CoSb3-compound will be dealt with in a sepa-

rate paper.

There are 4 figures, and 15 references, 8 of which are Slavic.

ASSOCIATION: Institute of Metallurgy imeni A. A. Baykov AS USSR. Moscow (Institut

metallurgii imeni A. A. Baykova AN SSSR Koskva).

SUBMITTED: Har

Earch 21, 1957.

AVAILABLE:

Library of Congress.

1. Cobalt alloys-Analysis 2. Antimony alloys-Analysis

Card 4/4

CIA-RDP86-00513R000411430001-7

DUDKIE, L.D.; ARRIKOSOV, M.Rh.

Alloying the semiconducting compound CoSb3. Fix.tver.tela 1 no.1:142-151 Ja *59. (MIRA 12:4) (Semiconductors) (Cobalt antimonides)

507/78-4-10-22/40 5(2) Dudkin, L. D., Dyul'dina, K. A. AUTHORS: Investigation of the System Cobalt - Tellurium TITLE: PERIODICAL: Zhurnal neorganicheskoy khimii, 1959, Vol 4, Nr 10, pp 2313 - 2319 (USSR) Among the binary compounds with semi-conductor properties the ABSTRACT: substances of the type metal transition -semi-conductor (metal transition transition metals, semi-conductor = semiconductor elements of the 3rd - 7th group of the periodic system) form a special group which has been little investigated so far. N. Kh. Abrikosov et al (Refs 1-3) carried out some investigations on antimonides. The present paper continues this series. A number of Co - Te-melts was investigated (Table 1) and the phase diagram was constructed (Fig 2). The system shows two interphases. The Y-phase melts with open maximum at approximately 10100, the 0-phase corresponds to the compound CoTe2 and is caused by the peritectic reaction 3 24 + liquid at 7490. The Y-phase forms with Co an eutectic melting at 9600. The investigation of the micro-structure (Fig 4) confirmed the data of the thermal ana-Card 1/2

Investigation of the System Cobalt - Tellurium

507/78-4-10-22/40

lysis. The radiograph (Fig 5) reproduce well the phase transition at increasing tellurium concentration. The thermoelectric properties of the melts reveal distinctly the boundaries of the X-phase. The continuous variation within the phase itself indicates the berthollid-like character of the structure. Since the number of structural defects of the X-phase is of the same order of magnitude as the number of atoms, no semi-conductor properties may be expected. Both the X- and d-phase have apparently a metal structure. The J-phase possesses a marcasite lattice, the X-phase a lattice derived from CdJ. (1) Abstracter's Note: disordered transition structures are denoted as berthollids (derived from the French chemist Berthollet). There are 6 figures, 1 table, and 11 references, 5 of which are Soviet.

SUBMITTED: June 21, 1958

Card 2/2

5(2,4)

AUTHORS: Dudkin, L. D., Ostranitsa, A. P.

807/20-124-1-26/69

TITLE:

Ternary Semiconducting Compounds Coming Under the General Formula AlbyByl (Troynyye poluprovodnikovyye soyedineniya

 $A^{I}B^{V}B_{2}^{VI}$)

PERIODICAL:

Doklady Akademii nauk SSSR, 1959, Vol 124, Nr 1, PP 94 - 97 (USSR)

ABSTRACT:

The compounds mentioned in the title are formed on the basis of binary compounds from which one at least must be a semiconductor. The ratios of the molar concentrations between the initial components correspond to those of simple integers. The present paper deals with the elucidation of the existence and of the physical chemical nature of the hypothetic compounds under review where A iscu, Ag, B - Sh Bi, and BVI - Se, Te (Ref 1). Their formation is assumed from analogies with the

chalcopyrite-like group of semiconducting compounds

in ternary systems AI - BV - BVI on quasibinary at a ratio of the components of

Card 1/3

Ternary Semiconducting Compounds Coming Under the General Formula ${\bf A}^T{\bf B}^V{\bf B}_2^{VT}$

SOV/20-124-1-26/69

1:1, AIII being Al, Ga, In, Tl. In spite of the related chemical composition of and AIAIIIB it may easily be stated that they are not isostructural. On the basis of corresponding binary compounds 8 ternary alloys were produced. Their composition is given in table 1. The investigation was performed according to a method similar to that described in reference 2. It was found that 4 compounds only: CuSbSe2, AgSbSe2, AgSbTe2 and AgBiSe2 do really exist. They crystallize direct from the melt. The microstructure of the alloys CuSbTe, and CuBiTe, is of sutectic nature; CuBiSe, and AgBiTe, have proved to be two-phase alloys. The heating- and cooling curves were constructed on one-phase alloys and the crystallization temperatures of the ternary compounds were determined from those curves (Table 2). The congruent character of the molting was confirmed. Table 2 shows the estimated coefficients of thermal conductivity. The determination results of the electric conductivity of the compounds under review as a function of temperature are given in figure 1.

Card 2/3

Ternary Semiconducting Compounds Coming Under the General Formula $A^{\mathsf{T}}B^{\mathsf{Y}}B_2^{\mathsf{Y}\mathsf{I}}$

SOV/20-124-1-26/69

CuSbSe, AgSbSe, and AgBiSe, show dependences $\sigma(T)$ which are characteristic of semiconductors. By means of $\sigma(T)$ the activation energies of the current carriers in ternary compounds were calculated (Table 2). Powder-radiographs were taken. From the assumption that the scheme of the bindings (Fig 2) is characteristic of all compounds mentioned in the title, the authors deduced the qualitative conditions which determine their stability. There are 2 figures, 2 tables, and 5 references, 4 of which are Soviet.

ASSOCIATION: Institut metallurgii im. A. A. Baykova Akademii nauk SSSR

(Institute of Metallurgy imeni A. A. Baykov of the Academy of

Sciences USSR)

PRESENTED:

August 8, 1958, by I. P. Bardin, Academician

SUBMITTED:

July 29, 1958

Card 3/3

AUTHOR:

Dudkin, L. D.

507/20-127-6-16/51

TITLE:

On the Problem of Formation of the Semiconductor Phase in

Systems With Transition Metals

PERIODICAL:

Doklady Akademii nauk SSSR, 1959, Vol 127, Nr 6, pp 1203-1206

(USSR)

ABSTRACT:

In the introduction, it is pointed out that the difference in conductivity of semiconductor compounds, one component of which is a transition metal, lies in the energy spectrum of the valency-d-electrons. In a number of papers, it was suggested to relate the conductivity with the existence or absence of an overlapping of the d-shells. It is suggested here to express in relative units the overlapping of the valency-d-shells in the atoms of the transition metals by some defined critical spaces between the valency shells. This value A is defined as a function of the distances between the atoms of the transition metals and their diameters, and these values are given for 21 compounds in table 1. All compounds with $\Delta > 14.5\%$ show semiconductor properties. Compounds with the structure type of NaCl are listed as examples in table 2; they all show semiconductor properties, and their value of A is larger than 14.5%. The silicon compounds of

Card 1/2

307/20-127-6-16/51 On the Problem of Formation of the Semiconductor Phase in Systems With Transition Metals

> the transition metals of the fourth to sixth groups are compiled in table 3 which shows that only CrSi, has semiconductor properties, and that its value of Δ is the only one in this group exceeding 14.5%. Besides, the temperature dependence of CrSb is investigated, and the measurement results are compiled in a table. Finally, some further results of this investigation are discussed, and it is ascertained that the criterion obtained here can be used in the search for new semiconductor materials. There are 4 tables and 18 references, 7 of which are Soviet.

ASSOCIATION: Institut metallurgii im. A. A. Baykova Akademii nauk SSSR (Institute of Metallurgy imeni A. A. Baykov of the Academy

of Sciences, USSR)

March 16, 1959, by I. P. Bardin, Academician PRESENTED:

March 5, 1959 SUBMITTED:

Card 2/2

ZOBNINA, B.W., DUDKIN, L.D.

Investigating the thermoelectric properties of the compound CoSb₃ with the electroactive impurities Sn, Te, and Hi. Fig. tver.tela 1 no.12:1821-1827 D '59. (MIRA 13:5)

1. Institut metallurgii imeni A.A. Baykova AN SSSR, Moskva. (Gobalt antimonide)

"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7

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S/181/60/002/03/04/028 B006/B017

AUTHOR:

Dudkin, L. D.

TITLE:

Crystallochemical Characteristic Features of Semiconducting

Compounds of Transition Metals

PERIODICAL:

Fizika tverdogo tela, 1960, Vol. 2, No. 3, pp. 397-403

TEXT: In the present paper, the author suggests two additional criteria for the formation of semiconducting phases in systems with transition metals, and on the basis of these phases the character of conductivity of a number of compounds having the structure of NiAs, NaCl, CrSi2, MoSi2, CuAl2, and PeS2 is explained or predicted. On the basis of the assumption that the degeneration of electronic energy states in the band takes place during chemical interaction, i.e., when the exchange effect is realized by electrons, as is the case with a critical interatomic distance, the following quantitative criterion is given, which determines the energy state of d-electrons in transition metal compounds. The type of conductivity is determined by the amount of

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Crystallochemical Characteristic Features of Semiconducting Compounds of Transition Metals

S/181/60/002/03/04/028 B006/B017

 $\Delta = \frac{(M-M)-d_M}{(M-M)} \cdot 100 ; \quad \Delta \text{ is given in } \%, \quad (M-M) \text{ is the least interatomic}$

distance of the transition metal in the compound, and d_M is the diameter of the metal atoms for the coordination number of this compound. The change of the d-electron spectrum from the band type to a discrete character takes place with relative distances between the valence shells of the metal atoms corresponding to $\Delta \approx 14.5\%$. When $\Delta < 14.5\%$ the wave functions of the d-electrons overlap, and the energy levels in the band are degenerate. In this case the compound has metallic conductivity, irrespective of the binding character metal-metal, due to the "free" electrons in the d-band. When $\Delta \ge 14.5\%$ the d-electrons occupy the discrete energy levels and do not participate in conduction. If, furthermore, the condition of a saturation of covalent bonds is satisfied, compounds with $\Delta > 14.5\%$ were bound to be semiconductors. The Tables contain the Δ -values for a number of compounds, and their known or theoretically predicted type of conductivity is given. Hence, metallic

Card 2/4

Crystallochemical Characteristic Features of Semiconducting Compounds of Transition Metals

S/181/60/002/03/04/028 B006/B017

character is predicted for TIS, CoS, and MIS, and semiconductor character for VPVand FeSevaccording to this criterion. The second criterion for the formation of semiconducting phases in systems with transition metals refers to compounds in which the metal atoms form octahedral hybrid d2sp3 bonds. With the exception of FeS2 itself, all compounds of this structure have a A which is higher than the critical one. It may be assumed that in these compounds the metal atoms form hybrid d2sp3 bonds and the atoms of the electronegative component sp3 bonds. The general scheme of the bonds between the atoms of FeS2-type compounds is shown in Fig. 1. It may be concluded from the bond types that manganese and iron dichalcogenides have semiconductor character, whereas the corresponding cobalt and nickel compounds have a metallic one (Table 6). Academician A. F. Ioffe, I. S. Zolotarev, V. G. Lev, K. A. Dyul dina. and V. I. Vavdanich are mentioned. There are 2 ligures, o tables, and 19 references: 8 Soviet, 3 British, 2 Canadian, and 1 Japanese.

Card_3/4

"APPROVED FOR RELEASE: 08/25/2000

CIA-RDP86-00513R000411430001-7

Crystallochemical Characteristic Peatures of Semiconducting Compounds of Transition Metala

81350 S/181/60/002/03/04/028 B006/B017

ASSOCIATION: Institut metallurgii im. A. A. Baykova AN SSSR (Institute of Metallurgy imeni A. A. Baykov of the AS USSR)

SUBMITTED: June 23, 1959

Card 4/4

S/181/60/002/03/05/028 B006/B017

24.7700 AUTHORS:

Dudkin, L. D., Vaydanich, V. I.

TITLE:

The Character of Electrical Conductivity of Some Compounds of Transition Metals With CuAl2-Type Lattice

PERIODICAL:

Fizika tverdogo tela, 1960, Vol. 2, No. 3, pp. 404-405

TEXT: In Refs. 1,2 the authors gave criteria for the formation of semiconducting phases. One of them is connected with the possible change in the energy spectrum of unbound d-electrons, and the conduction type is

determined by the value of $\Delta = \frac{(M-M)-d_M}{(M-M)}$ -100, where (M-M) is the

shortest distance between two atoms of transition metals, and $d_{\rm H}$ the diameter of metal atoms. If $\Delta < 14.5\%$ the compound shows metallic conductivity, if $\Delta > 14.5\%$ it is a semiconductor. Hence, the compounds knSn₂, FeSn₂, CoSn₂, TiSb₂, and VSb₂ were bound to have metallic conductivity (see Table p.404). For the purpose of examining this problem

Card 1/3

The Character of Electrical Conductivity of Some Compounds of Transition Metals With CuAl2-Type Lattice

81351 \$/181/60/002/03/05/028 B006/B017

the authors analyzed these compounds for the type of their conductivity. The production of the specimens is described in detail. A thermal analysis of the heating of the equilibrium specimen and the cooling of the melt showed that the incongruent melting temperatures of TiSb₂ and VSb₂ are 1,010 and 900°C; crystallization starts at 1,030 and 1,120°C, respectively. In VSb₂, an additional effect was observed at 870°C (polymorphic transformation). In all alloys, conductivity and the coefficient of the thermomal were measured; the results are in agreement with the conductivity types predicted according to A. For VSb₂ and FeSn₂ which showed the least conductivity, the temperature course was recorded (Fig.). The values of and a at room temperature and the course of the curve o(T) also indicate metallic conductivity. There are 1 figure, 1 table, and 5 references: 2 Soviet, 1 US, and 2 German.

ASSOCIATION: Institut metallurgii im. A. A. Baykova AN SSSR Moskva (Institute of Metallurgy imeni A. A. Baykov of the AS USSR, Moscow)

Card 2/3

The Character of Electrical Conductivity of Some Compounds of Transition Metals With CuAl2-Type Lattice

81351 S/181/60/002/03/05/028 B006/B017

SUBMITTED:

August 11, 1959

Card 3/3

Dudkin, L.D.

8/181/60/002/007/022/042 B006/B060

AUTHORS:

Dudkin, L. D., Vaydanich, V. I.

TITLE:

The Character of the Chemical Bonds and the Electrical Conductivity of Compounds of the FeS2 Structural Type

PERIODICAL:

Fisika tverdogo tela, 1960, Vol. 2, No. 7, pp. 1526-1532

TEXT: The authors wanted to study the thermoelectric properties of a series of compounds of this group with antimony, tellurium, and selenium in order to establish whether the atoms of the transition metals in these compounds have hybrid-d sp bonds. The results of relevant papers are discussed in the introduction, and next, the authors discuss the methods of preparing the specimens and of conducting the investigation. The initial substances exhibited a high degree of purity. The specimens obtained after complicated melting, annealing, pulverisation, and pressing treatments, and final thermal treatment were submitted to a microstructural and a thermal analysis (with a pyrometer by N. S. Kurnekov). The electrical resistivity and the thermo-emf were measured in a compensating circuit with a potentiometer of the type WHTE-1 (PPTV-1). The magnetic susceptibility was

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The Character of the Chemical Bonds and the Electrical Conductivity of Compounds of the FeS, Structural Type

S/181/60/002/007/022/042 B006/B060

determined by a balance method. The microstructure of cast specimens is shown in Fig. 1 (FeTe2) and Fig. 2 (MnTe2) A The specimens with selenium (FeSe, and CoSe,) exhibited a highly distorted peritectic picture (Table 1). To investigate the thermoelectric properties it was necessary to prepare special test pieces; the data of the specimens exhibiting the highest conductivity are tabulated in Table 2. Only $\cos_2(\sigma > 10^5 \text{ ohm}^{-1} \cdot \text{cm}^{-1})$ showed metallic conductivity, the other four (FeSta, MnTe2, FeTe2, and FeSe2) proved to be semiconductors. To get a closel insight and to determine the activation energy of the carrier, the temperature dependence of electrical conductivity was examined. Figs. 3 - 6 show this for the four compounds. The curves $\ln c = f(T)$ show two salient points for FeSe, which, referred to the range of intrinsic conductivity, points to different values of the activation energy, i.e., two bond types: a weak type (Se-Se with $\Delta E = 0.60$ ev) and a strong one (Pe-Se with $\Delta E = 0.95$ ev). The width of the forbidden band (0.37 ev) corresponds to an impurity activation. A determination of susceptibility (Fig. 7) indicates that FeSe, is weakly Card 2/3

The Character of the Chemical Bonds and the Electrical Conductivity of Compounds of the FeS, Structural Type

3/181/60/002/007/022/042 B006/B060

ferromagnetic. The results are discussed in the final part of the paper and compared with those of other authors (Table 3). The results obtained by considerations on the binding character are shown in a figure (Fig. 8). There are 8 figures, 3 tables, and 18 references: 7 Soviet, 2 US, 2 German, 1 Canadian, 1 Japanese, and 3 Scandinavian.

ASSOCIATION:

Institut metallurgii im. A. A. Baykova AN SSSR Moskva (Institute of Metallurgy im. A. A. Baykov of the AS USSR,

Moscow)

SUBMITTED:

October 2, 1959

CIA-RDP86-00513R000411430001-7" APPROVED FOR RELEASE: 08/25/2000

S/576/61/000/000/015/020 E021/E120

AUTHORS:

Dudkin, L.D., and Vaydanich, V.I.

TITLE:

Electro-physical properties of several compounds of

the transition metals of the type MrB2

SOURCE:

Soveshchaniye po poluprovodnikovym materialam, 4th. Voprosy metallurgii i fiziki poluprovodnikov; poluprovodnikovyye soyedineniya i tverdyye splavy. Trudy soveshchaniya. Moscow, Izd.-vo AN SSSR, 1961. Akademiya nauk SSSR. Institut metallurgii imeni A.A. Baykova. Fiziko-tekhnicheskiy institut. 113-122

TEXT: The present work gives results of a study of the electro-physical properties of compounds of the transition metals (MT) in the series Ti-Ni and tin, antimony, selenium or tellurium (denoted by B). The compounds have the structure MTB2. The initial materials were: 99.98% Ti, 99.0% V, 99.97% Cr, 99.9% Mn, 99.99% Co, 99.999% Ni, 99.999% Sn, 99.999% Sb, 99.98% Se, and 99.9% Te. The compounds were synthesized in evacuated quartz vessels, with the exception of compounds of titanium. The most suitable material for use with titanium was found to be Card 1/3

Electro-physical properties of S/576/61/000/000/015/020 E021/E120

zirconium oxide. The samples of FeSb2, TiSb2 and VSb2 were homogenized at 550-630 °C for 30-35 days. The alloys containing tin, tellurium and selenium were heated gradually from 200 °C to 450 °C, with the total heat-treatment time of 45-50 days for selenium and tellurium alloys and 90 days for tin alloys. Measurement showed that compounds with CuAl2-type structure (MnSn2, FeSn2, CoSn2, TiSb2 and VSb2) possessed metallic type of conduction. Compounds with FeS2-type structure (FeSb2, MnTe2, FeTe2 and FaSe2) were semiconductors except for CoSe2 which possessed metallic properties. The results of measurements on compounds with CdI2-type structure (TiFe2, CrTe2 and NiTe2) were considered in more detail. X-ray and thermal analyses were carried out together with electrical and magnetic measurements. It was shown that only chromium ditelluride possessed semiconducting properties. TiTe2 and NiTe2 possess metallic type of conduction. The results of the thermal analysis are given in Table 2. A probable form of the phase diagram is constructed for the system Mr-B showing continuous transition between 1:1 compounds (NiAS type) and 1:2 compounds (CdI2 type). Hypothetical schemes for the inter-atomic bonds in Core core. Card 2, 3

Electro-physical properties of ...

\$/576/61/000/000/015/020 E021/E120

and also for the transition compounds NiTe and NiTe2 are presented,

There are 9 figures, 3 tables and 14 references: ? Soviet-bloc and 7 non-Soviet-bloc. The English language references read as

Ref. 1: M. Hansen. Constitution of binary alloys. New York, 1958.

Ref. 11: E. Mooser, W.B. Pearson, J. of Electr., 1956, v.1, 629.

Ref. 12: W.B. Pearson, Canad. Journ. of Phys., 1957, v. 35, 886.

		Table 2					
Compound	Temperature of Liquidus, ^C C	Temperature of Solidus, °C					
TiTe2	> 1250	~ 470					
CrTe ₂	1194	~ 540					
NiTe ₂	857	~ 600					

Card 3/3

5 2400 1087, 1043 2205

30028 S/020/61/141/001/010/021 B103/B147

AUTHORS:

Dudkin, L. D., and Kuznetsova, Ye. S.

TITLE:

Study of the system Mn - Si in the range rich in silicon

PERIODICAL: Akademiya nauk SSSR. Doklady, v. 141, no. 1, 1961, 94 - 97

TEXT: The existence of MnSi₂ in the system Mn-Si is not sufficiently founded (Ye. N. Nikitin, Piz. tverd. tela, 1, 340 (1959)), and the data on the formation of the disilicide and on the phase diagram are contradictory. For these reasons, the authors studied the range rich in Si of the system Mn-Si. They used Si (99.998%) prepared according to Beketov [Abstracter's note: method not stated] and electrolytic Mn remelted twice in vacuo with traces of Al, Si, and Cu, as well as with <0.001% Pb, Mo, Ti, and Co. Phases corresponding to the phase diagram were synthesized by melting together the initial components in evacuated and sealed quartz ampuls by means of high-frequency heating. After cooling in air the samples were annealed under argon at 1000°C for 200 hr. Heating curves for equilibrium samples were plotted at 600 and 1200°C, Card 1/34

30028 S/020/61/141/001/010/021 B103/B147

Study of the system Mn - Si...

and a thermal analysis was conducted. Sample and standard (Si) were molten in evacuated Stepanov vessels [Abstracter's note: vessel not stated]. The series of alloys produced contained 46 - 55% Mn. It was found that cast and annealed MnSi, samples were not monophase but contained considerable Si separations. On the basis of the microstructure of samples rich in Si, no MnSi2 phase was found to occur in the system Mn-Si. Neither were there any phase transformations in the range of primary Si crystallization. In alloys richer in Mn, a transformation is supposed to occur in the corresponding part of the system, which leads to a homogeneity of the sample with 46% Si. This Si content corresponds to the stoichiometric ratio of components of 3:5. Further, Mn3Si5 was found to have a narrow homogeneity range which corresponds to a dissolution of about 0.5% of excess Si and Mn atoms in the compound. Fig. 2 shows the phase diagram for part of the system. Crosses denote the thermal effects of M. Hansen (Ref. 5, see below). The diagram shows that Mn Si is formed by a peritectic reaction from MnSi and from the liquid at 1159°C. The eutectic of Mn_3Si_5 with Si corresponds to a Si content of $\sim49\%$, and melts

Card 2/1

S/020/61/141/001/010/021 B103/B147

Study of the system Mn - Si...

at a temperature some 10 °C lower (~1149°C). The composition of this compound is very similar to that of the liquid phase which corresponds to the nonvariant peritectic transformation. For this reason, the formation process of Mn3Si5 takes place during crystallization, and the cast samples do not show the characteristic patterns as correspond to the hardened peritectic transformation. These conclusions were confirmed by Debye patterns. A narrow homogeneity range on the basis of Mn_Si_5 causes a complicated dependence of the thermoelectric properties on Si content. The dissolution of excess Mn and Si atoms is accompanied by the formation of additional current carriers. This is assumed to be connected with the formation of a defective lattice. The assumption is confirmed by a considerable increase in electrical conductivity in the range of the solid solution. The thermo-emf increases slightly at the same time. The change of the thermoelectric characteristics in the two-phase range is due to the effect of different secondary phases. Up to about 500°C, a metallic dependence lno(1/T) prevails; at higher temperatures, the measured values lie on a straight line. The activation energy of the current carriers is~0.2 ev. A. S. Berezhnoy's monograph: Kremniy i yego binarnyye sistemy Card 3/\$ 4

30028 S/020/61/141/001/010/021 B103/B147

Study of the system Mn - Si...

(Silicon and Its Binary Systems), Kiyev, 1958, is mentioned. There are 4 figures and 5 references: 4 Soviet and 4 non-Soviet. The reference to the English-language publication reads as follows: Ref. 5: M. Hansen, Constitution of Binary Alloys, N. Y., 1958.

ASSOCIATION: Institut metallurgii im. A. A. Baykova Akademii nauk SSSR

(Institute of Metallurgy imeni A. A. Baykov of the

Academy of Sciences USSR)

PRESENTED: June 12, 1961, by I. I. Chernyayev, Academician

SUBMITTED: June 8, 1961

Card 4/9 4

8/849/62/000/000/010/016 A006/A101

AUTHOR:

Dudkin, L. D.

TITLE:

Some regularities in the formation of semiconductor phases in

systems with transition metals

SOURCE:

Vysokotemperaturnyye metallokeramicheskiye materialy, Inst.

metalloker, i spets, spl. AN Ukr, SSR., Kiev, Izd-vo AN, Ukr, SSR. DE

87 - 95

TEXT: In semiconductor compounds, the intermediate phases in systems with transition metals and elements of the IV - VII group (Me trans - B), have not been sufficiently studied. It was experimentally found that shows absence to the

been sufficiently studied. It was experimentally found that sharp changes in the nature of conductivity were caused by varying chemical composition, the bond type of M_{trans} - B remaining constant. Therefore additional criteria, character-

izing the nature of conductivity in phases of the aforementioned systems were to be determined. The author assumes that the energy state of d-electrons can change from a discrete to a zonal state with variying distances between metallic atoms

Card -1/3-

Some regularities in the formation of ...

\$/849/62/000/000/010/016 A006/A101

in the crystals of corresponding compounds and thus entail changes in the type of conductivity. Two additional criteria were developed: Critical value \triangle determines changes in the energy spectrum of d-electrons. It is $\frac{\text{(Mo-Mo)}}{\text{(Mo-Mo)}} \cdot \frac{\text{(Mo-Mo)}}{\text{(Mo-Mo)}} \cdot \frac{\text{(M$

(Me-Me)

14.5%. (Me-me) is the shortest distance between metal atoms in the compound;
do is the diameter of metal atoms for the coordination number, corresponding to the given compound. If \$\infty\$ (14.5%), the d-electrons will determine the metal conductivity type of the compound; if \$\infty\$ 14.5% the d-electrons do not participate in the conductivity. The compound will then be semiconductor, in case of saturated trans - B bonds. The second criterion is applicable to systems where the metallic atoms form hybridic desp octahedral bonds. In this case the number of electrons participating in the formation of metal - non metal bonds, should not exceed 6. With the use of these two criteria the nature of conductivity is explained and predicted for a number of structural type systems, including NiAs, NaCl, CrSi2, CuAl2 and PeS2. The results are graphically illustrated. There are 6 tables and 2 figures.

Card 2/3

	. :	
\$/849/62/000/000/010/016		1
Some regularities in the formation of A006/A101 Figure 2. Scheme of bonds in cobalt triantimonide and electron-valent schemes of additional iron and nickel atoms, substituting cobalt in CoSb ₂ .		11
Sb 1 1 5p CoSb,		
	1	- Q
3d ¹ 454p ³	*	-
inactive (wowners)		
electro-active Grantor 3d 4s 4p 4d donor muchael dress	Arministry African as as as a second	

DUDKIN, L.D.; KUZHETSOVA, Ye.S.

Investigating the electrophysical properties of alloys on a base of chromium and manganese semiconductor disilicides. Porosh. met. 2 no.6:20-31 N-D 162. (MIRA 15:12)

1. Institut metallurgii imeni A.A.Baykova AN SSSR.
(Semiconductors—Thermal properties) (Chromium-silicon alloys)
(Manganese-silicon alloys)

"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7

ACC NR: AP7005615 SOURCE CODE: UR/0413/67/000/002/0052/0053 INVENTOR: Belevtsev, A. T.; Dudkin, L. D.; Yerofeyev, R. S.; Lidorenko, N. S.; Khanin, M. A. ORG: none TITLE: A method for manufacturing thermoelements. Class 21, No. 190448 [announced by the All-Union Scientific Research Institute of Current Sources (Vscsoyuznyy nauchno-issledovatel'skiy institut istochnikovtoka)] SOURCE: Izobreteniya, promyshlennyye obraztsy, tovarnyye znaki, no. 2, 1967, 52-53 TOPIC TAGS: thermocouple, temperature sensitive element, CURRENT CARRIER ABSTRACT: A method of making thermocouples with a variable concentration of electric current carriers along the operating temperature gradient is introduced. To assure both optimum variable concentration of the carriers and thermodynamic stability of the elements, the amount of alloying impurities in the carrier concentration is determined by the specific solubility of the alloying impurities, thus assuring the desired relationship between the carrier concentration and temperature-i.e., $n = T^3/4$. [JR] SUB CODE: 09/ SUBM DATE: 29Jul65

APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7"

UDC: 621.362.1

Card

ACC NR. AP7004401

SOURCE CODE: UR/0226/67/000/001/0073/0080

AUTHOR: Voronov, B. K. (Moscow); Dudkin, L. D. (Moscow); Kiryukhina, N. I. (Moscow); Trusova, N. N. (Moscow)

ORG: none

TITLE: Study of the Cr-Si system in the disilicide region

SOURCE: Poroshkovaya metallurgiya, no. 1, 1967, 73-80

TOPIC TAGS: chromium, silicon, system, stoichiometric mixture, microhardness heat conductivity, carrier density, sensite crystal melecular defect, redensity, stoichiometry, personal melecular defect, redensity, stoichiometry, personal melecular defect, redensity, personal melecular description of the polyecystal, Coordinately method.

ABSTRACT: It was found that the chromium disilicide phase, crystallizing at CrSi_{1.95}, expands with a drop in temperature, shifts toward nilicon, and at 1250C corresponds to the saturated composition of CrSi_{1.98-1.99}— CrSi_{2.02-2.03} The stoichiometric composition corresponds to the minimum of microhardness, the maximum of heat conduction, the minimum value of hole concentration, the

Card 1/2

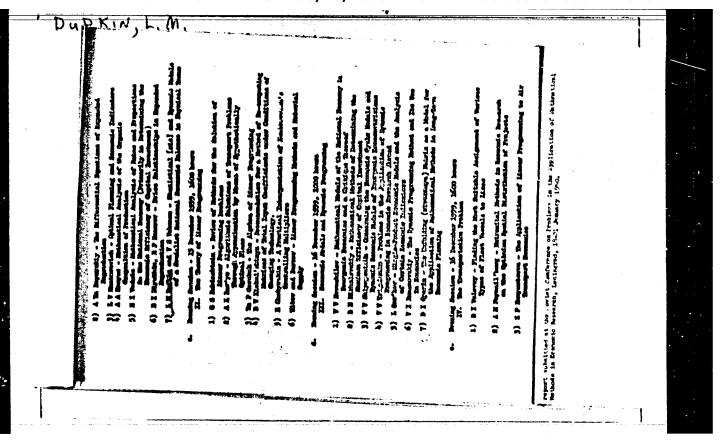
ACC NEI AP7004401

minimum effective density of states of the carriers, and the maximum value of the prohibited zone width, ~0.7 ev, which falls near the single-phase boundaries to 0.4—0.5 ev. It is assumed that the high hole concentration (5.10²⁰/cm³) in the stoichiometric mixture is due to intracrystalline defects. With deviation from stoichiometry toward chromium, the defects are reduced, and at CrSi_{1.95} of stretched single crystals, it approaches 0, while on deviation toward excess silicon, it remains approximately constant. One molecular defect yields from 0.5 to 1 carrier into the valence band. Orig. art, has: 2 figures and 2 tables. [Based on authors! abstract]

SUB CODE: 11/SUBM DATE: 30May66/ORIG REF: 013/OTH REF: 003/

Card 2/2

"APPROVED FOR RELEASE: 08/25/2000 CIA-RDP86-00513R000411430001-7



DUDKIN, L.M., red.; SHILIN, I.G., red.; YERMAKOV, M.S., tekhn. red.

[Problems of the optimal planning, prejection and administration of production] Problemy optimal'nego planirevaniia, proektirovaniia i upravleniia proisvedstvom; trudy teoreticheskoi konferentsii, sestoiavsheisia na ekonemicheskom fakul'tete MGU v marte 1962. Meskva, Isd-ve Mosk. univ., 1963. 546 p. (MIRA 16:9)

1. Teoreticheskaya kenferentsiya "Preblemy optimal'nogo planirovaniya, proyektirovaniya upravleniya proisvodstvom," 1962. 2. Meskovskiy Gosudarstvennyy universitet (for Shilin, Dudkin). (Russia—Economic policy)

CHICHELOKOV, YA.H.; INDEEN, L.H.; MAYAROU, A.C.

Do we need a cut-off valve? Caz. prom. 3 no. 11:37-35 163. (MTBA 17:11)

- 1. Uralenergenstallergprom, Sverdicvak (for Sechalekov).
 2. "Bryanskogsugas" (for butkin). 3. Usrasluniya tsentralinego oleuga Goauderstvennego komitein pri imela Ministro. Paffal poredram ze bezejacny: vedeniyem rabet v jeznychlennosti i gornozu nadsors (for Makares),

DUDMIN, MI.

IVANOV, N.A., professor; PANTAZI, V.D.; DUDKIN, M.I. (Leningrad)

Case of acanthosis nigricans. Vrach.delo no.7:753-755 J1 '57. (MLRA 10:8)

1. Kafedra koshnykh i venericheskikh bolesney (nach. - polkovnik meditsinskoy slushby professor S.Ye. Gorbovitskiy) Voyenno-morskoy meditsinskoy Akademii (SKIM--DISEASES)

KARDASHENKO, B. Ta.; OLISEVICH; V.E.; DUDKIN, H.I.

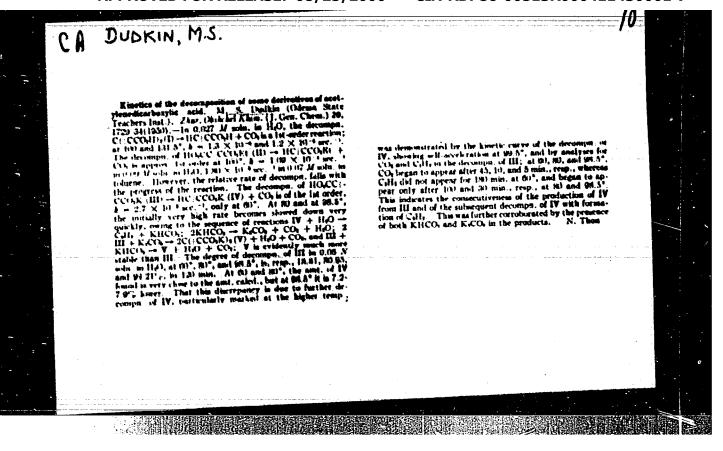
Local steroid therapy of some dermatoses. Sov.med. 25 no.1:125-127

1. Iz kozhnogo dispansera No.7 Kiyevskogo rayona Moskvy (glavnyy vrach B.Ya.Kardashenko). (SKIN-DISEASES) (STEROID HORMONES)

DIDKIN, M.S.

Xylan. Usp.khim. 31 no.10:1179-1190 0 '62. (MIRA 15:11)

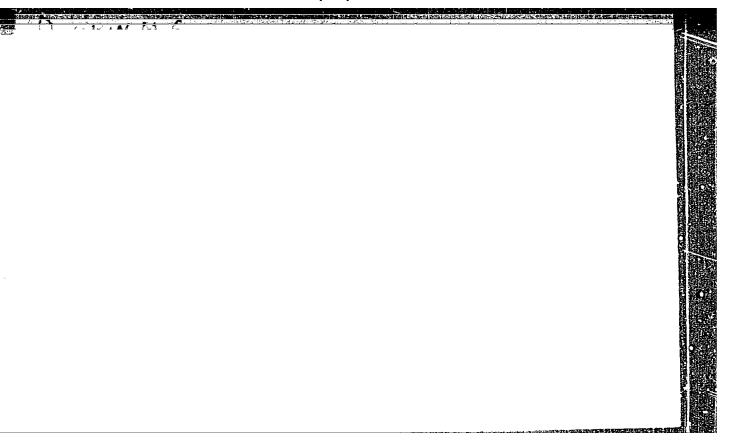
1. Odesskiy tekhnologicheskiy institut imeni Lomonosova. (Xylans)

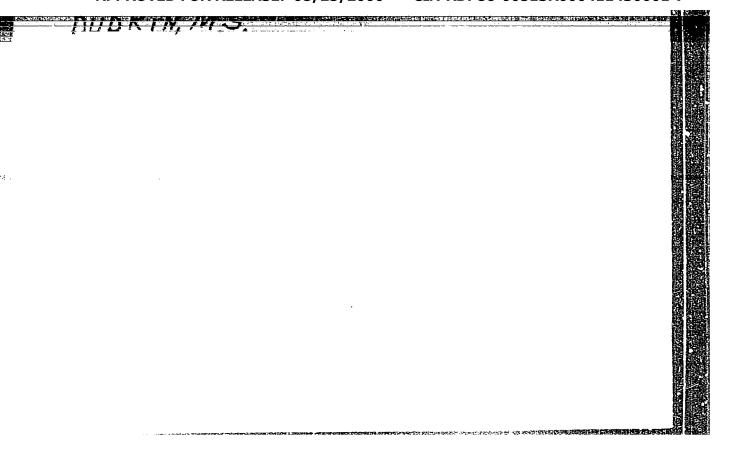


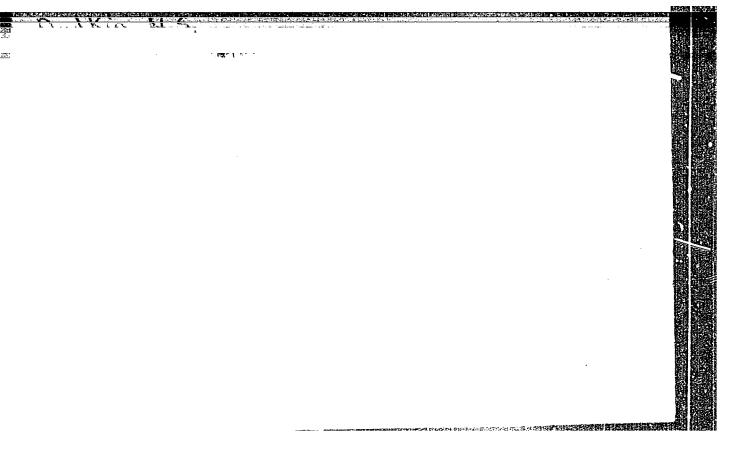
DUDKIN, M.S.; EMRISTMAN, R.Ya.

Quantitative determination of organic substances found in Black Sea seaweeds. Ukr.khim.shur.17 no.2:217-223 '51. (RIBA 919)

1. Odesekiy uchitel skiy institut. (Black Sen-Algae)







A-7

DUDKIN, M.S.

Category: Ukraine/General Division. Problems of Teaching.

Abs Jour: Referat Zh.-Biol., No 9, 10 May, 1957, 35002

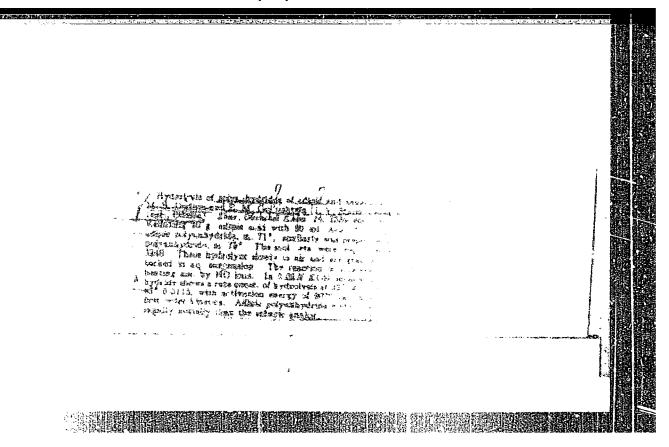
Author : Dudkin, M.S.
Inst : not given

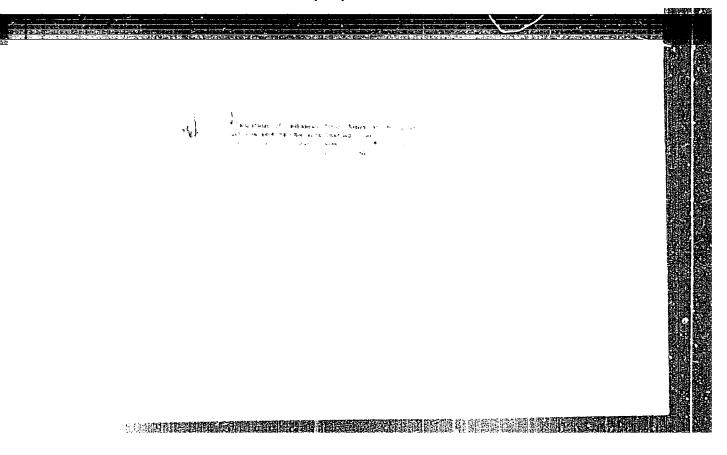
Title : The Study of the Chemical Composition of Corn in Secondary Schools

Orig Pub: Radyanska shkola, 1956, No 1, 63

Abstract: No abstract.

Card : 1/1





DUDKIN, M.S.; SHELOVSKIY, I.Sh.

Rydrolymis of hemicelluleses in the lemmas of barley. Isv. vys. ucheb. sav.r pishchi tekh. no.1136-42 158. (KIEA 1218) ucheb. sav.; pishch, tekh, no.1:36-42 158.

1. Olesakiy tekhnologicheskiy institut imeni I.V. Stalina, Kafedra organicheskoy khimii.
(Barley) (Hemicellulose) (Hydrolysis)

DUDERS, M.S.

Chromatographic snalysis of monosaccharides found in miliet lemmas and buckwheat bulls. Isv. vys.ucheb. sav.; pishch. tekh. no. 2:147-150 *58. (MIRA 11:10)

1. Odesskiy tekhnologicheskiy institut imeni I.V.Stelina, Kafedra organicheskoy khimii.

(Monosaccherides) (Millet) (Buckwhest)

DUDKIN, M.S.; STARICHKOVA, V.Ye.

Effect of the vibration milling on the hydrolysis of polysaccharides of millet hulls. Isv.vys.ucheb.sav.;pishch.tekh. no.5:105-109 '58. (MIRA 11:12)

1. Odesekiy tekhnologicheskiy institut imeni I.V.Stalina, kafedra organicheskuy khimii. (Millet) (Polymaccarides) (Hydrolymis)

80319

5.3832

SOV/81-59-7-26009

Translation from: Referativnyy zhurnal, Khimiya, 1959, Nr 7, p 610 (USSR)

AUTHOR:

Dudkin, M.S.

TITLE:

High-Molecular Compounds on the Base of Acyl Derivatives of Urea. Communication IV. The Interaction of Acetylurea With Formaldehyde

FERIODICAL: Tr. Odessk. tekhnol. in-ta im. I.V. Stalina, 1958, Vol 9,

pp 45 - 48

ABSTRACT:

During the interaction of acetylurea (I) with formaldehyde (II) at first methylolacetylurea is formed which condenses later on forming $(-N(COCH_3)CONH-CH_2)_n$ with a polymerization degree of 5 - 6 and a molecular weight of 600 - 700. The value of the specific viscosity of the polycondensate depends on the nature of the solvent and is caused by its polarity. The following values are cited below: the solvent, its dipole moment M.1018, the specific viscosity of the product of interaction of I with II obtained in the absence of a catalyst and in the presence of NH_AOH: acetone (III), 2.95; 0.0714; 0.0536; ethanol, 1.70;

Card 1/2

80319

sov/81-59-7-26009

High-Molecular Compounds on the Base of Acyl Derivatives of Urea. Communication IV. The Interaction of Acetylurea With Formaldehyde

0.063; 0.1315; dioxane, 0.4; 0.4781; 0.1575. The highest value of viscosity in III is due to considerable solvation which makes the aggregation of the molecules difficult. In dioxane, in the case of low solvation of the solvent, the degree of aggregation attains a high value which leads to an increase in the viscosity of the solvent. Communication III see RZhKhim, 1957, 52733.

Ye. Rodionova

Card 2/2

DUDEIH, M.S. (Odessa) Polysulfide rubber. Khim. v shkole 13 no.5:57-59 8-0 (MIRA 11:9) (Rubber, Synthetic)

DUDIIN, M.S., kand, tekhn, mank; SKORNYAKOVA, N.S., kand, khim, mank,

Fractional crystallisation of whale oil acids with urea. Masl.-shir. prom. 24 no.3:19-21 158. (NIRA 11:4)

1. Clesskiy tekhnologicheskiy institut imeni I.V. Stalina.
(Whale oil) (Acids, Fatty) (Urea)

DUDKIN, H.S.

Hydrolysis of hemicelluleses of millet flower pellicles and of bucksheat hulls. Isv.vys.ucheb.sav.; pishch.tekh. no3: 48-53 159. (MIRA 12:12)

1. Odesskiy tekhnologicheskiy institut imoni I.V.Stalina. Kafedra organicheskoy khimii. (Millet) (Bucksheat) (Hemicellulose)

DUDKIN, M.S.

12

Hydrolysis of the hemicellulose of barley and rice hulls. Isv.vys.ucheb.sav.; pishch.tekh. no.4:40-44 159.
(HIRA 13:2)

1. Odesakiy tekhnologicheskiy institut imeni I.V.Stalina. Kafedya organicheskoy khimii. (Hemicellulose) (Grain)

DUDEIN, M.S.; PILIPERED, L.S.

Prospects for the utilisation of pentosan-containing raw materials of the Odessa Province. Gidrolis.i lesokhim.prom. 12 no.8:25 '59. (MIRA 13:4)

1. Odesskiy tekhnologicheskiy institut (for Budkin). 2. Odesskiy sovnarkhos (for Pilipenko).
(Odessa Province-Pentosan)

5.3600

75692 SOV/80-32-10-41/51

AUTHOR:

Dudkin, M. S.

TITLE:

Brief Communications. Reaction of Adipic and Sebacic

Acids With Urea and Acetylurea

PERIODICAL:

Zhurnal prikladnoy khimii, 1959, Vol 32, Nr 10,

pp 2347-2348 (USSR)

ABSTRACT:

Reaction of adipic and sebacic acids with urea and acetylurea on heating was studied. Adipic acid with urea, at 160°, gave the diamide of adipic ncid, mp 224-225°, in 22.8% yield. The same reaction at 230° gave the same product in 32% yield. Sebacic acid with urea at 160° gave the amide of sebacic acid, mp 172-173°, in 32% yield. The same reaction at 230° gave the amidoureide of sebacic acid, mp 182-183°, in 34.5% yield. Adipic acid with acetylurea at 230° (molar ratio 1 to 1) gave the amide of adipic acid with mp 205-206°, in 26% yield. The same reaction (molar ratio of 1 sebacic acid to 2 urea) gave the diamide of sebacic acid, mp 223°, in 34% yield. Sebacic acid with acetylurea at 230° (molar ratio

Card 1/2

Brief Communications. Reaction of Adipic and Sebacic Acids With Urea and Acetylurea

75692 sov/80-32-10-41/51

1 to 1) gave the amide of sebacic acid with mp 172°, in 28% yield. The same reaction (molar ratio of 1 sebacic acid to 2 acetylurea) gave the diamide of sebacic acid, mp 208°, in 39% yield. There are 7 references, 3 Soviet, 1 German, 1 Swiss, 1 Indian, 1 U.S. The U.S. reference is: Roc, E., Scanlan, J., Swern, D., J. Am. Chem. Soc., 6, 2215 (1949).

SUBMITTED:

July 8, 1958

Card 2/2

VOROPATEVA, N.A.; DUDETE, M.S.

Anatomical structure of the flower pellicles of oat grain. Isv. vys.ucheb.sav.; pishch.tekh. no.1:17-22 '60. (MIRA 13:6)

1. Kafedra biokhimii serna i sernovedeniya i Kafedra organicheskey khimii Odesskoge tekhnologicheskege instituta imeni I.V. Stalina. (Oat)

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	DUDKIN, M.S.					
in the second se	Hydrolysis of hemicalluloses contained in grain husks in the presence of a cation exchanger. Ehur. prikl. khim. 34 no.1:199-204 Ja '61. (MIRA 14:1)					
		(Hemicellulese)		·		f_{ij}
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DUDKIN, M.S.; SKORNYAKOVA, M.S.; SHKANTOVA, M.G.

Action of nitrie acid on polysaccharides in grain halls and capsules. Zhur.prikl.khim. 34 no.10:2320-2327 0 161. (MIRA 14:11)

1. Kafedra organicheskoy khimii Odesskogo tekhnologicheskogo instituta imeni I.V.Stalina. (Hitric acid) (Polysaccharides)